

25V PNP MEDIUM POWER TRANSISTOR IN SOT223

Features

- BV_{CEO} > -25V
- I_C = -3A High Continuous Current
- I_{CM} = -8A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < -300mV @ -1A
- Complementary NPN Type: FZT649
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. https://www.diodes.com/quality/product-definitions/
- An Automotive-Compliant Part is Available Under Separate Datasheet (FZT749Q)

Mechanical Data

- Package: SOT223 (Type DN)
- Package Material: Molded Plastic. "Green" Molding Compound;
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 ³
- Weight: 0.112 grams (Approximate)

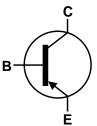
Applications

MOSFET and IGBT gate driving

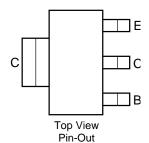




Top View



Device Symbol



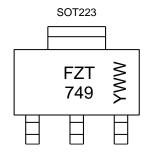
Ordering Information (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT749TA	Standard	FZT749	7	12	1,000
FZT749TC	Standard	FZT749	13	12	4,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



FZT 749 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)



Absolute Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-35	V
Collector-Emitter Voltage	V _{CEO}	-25	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ic	-3	Α
Peak Pulse Current	I _{CM}	-8	Α

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		3.0		
Dawar Dissipation	(Note 6)	D	2.0	W	
Power Dissipation	(Note 7)	P_{D}	1.6		
	(Note 8)		1.2		
	(Note 5)		41.7		
The arrest Desistance It westing to Archivet	(Note 6)	6	62.5		
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{ hetaJA}$	78.1	°C/W	
	(Note 8)		104		
Thermal Resistance Junction to Lead (Note 9)		$R_{ heta JL}$	12.9		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 10)

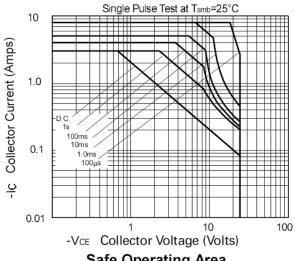
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	٧	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

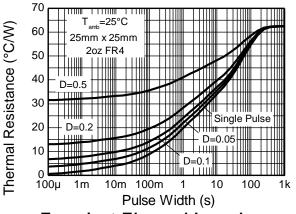
- 5. For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
- 7. Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
- 8. Same as Note 5, except the device is mounted on minimum recommended pad layout.
- 9. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



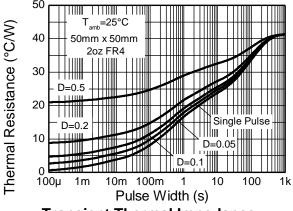
Thermal Characteristics and Derating Information



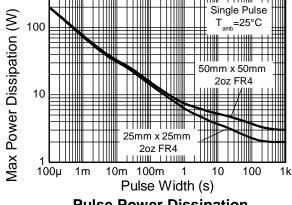
Safe Operating Area



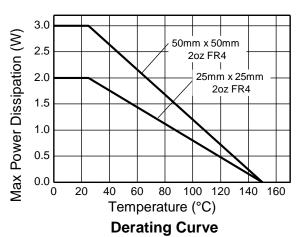
Transient Thermal Impedance



Transient Thermal Impedance



Pulse Power Dissipation



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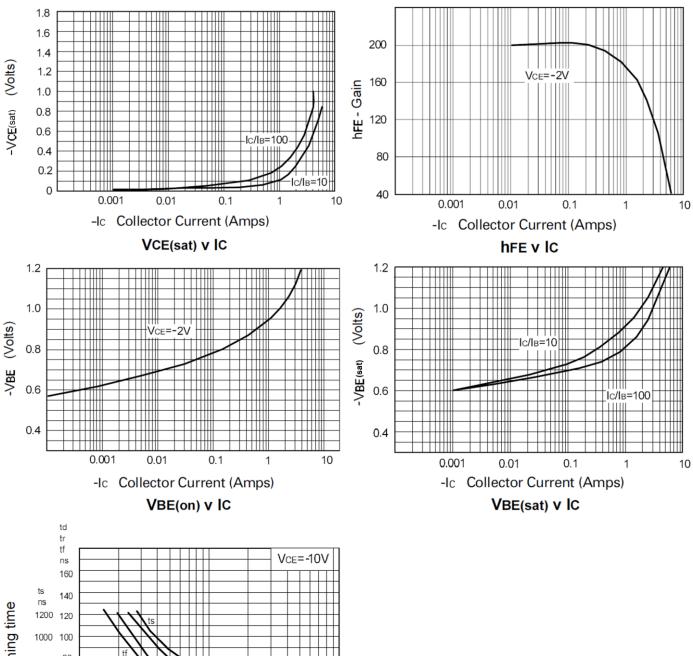
Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-35	_	_	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	-25	_	_	V	$I_C = -10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	_	_	V	$I_E = -100 \mu A$
Collector Cut-Off Current		_	-1	-100	nA	V _{CB} = -30V
Collector Cut-On Current	I _{CBO}	_	_	-10	μA	V _{CB} = -30V, T _{amb} = +100°C
Emitter Cut-Off Current	I _{EBO}	_	-1	-100	nA	V _{EB} = -5.6V
Collector Emitter Seturation Voltage (Note 11)		_	-0.12	-0.3	V	I _C = -1A, I _B = -100mA
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(sat)}	_	-0.40	-0.6] v	I _C = -3A, I _B = -300mA
Base-Emitter Saturation Voltage (Note 11)	V _{CE(sat)}	_	-0.9	-1.25	V	I _C = -1A, I _B = -100mA
Base-Emitter Turn-On Voltage (Note 11)	V _{BE(on)}	_	-0.8	-1.0	V	I _C = -1A, V _{CE} = -2V
		70	200	_		I _C = -50mA, V _{CE} = -2V
DC Current Coin (Note 11)		100	200	300		I _C = -1A, V _{CE} = -2V
DC Current Gain (Note 11)	h _{FE}	75	570	_	_	$I_{C} = -2A$, $V_{CE} = -2V$
		15	50	_		$I_C = -6A$, $V_{CE} = -2V$
Current Gain-Bandwidth Product (Note 11)	f _T	100	160	_	MHz	$V_{CE} = -5V, I_{C} = -100mA$ f = 100MHz
Turn-On Time	t _{on}	_	40		ns	V _{CC} = -10V, I _C = -500mA
Turn-Off Time	t _{off}	_	450	- ns $I_{B1} = -I_{B2} = -10$ mA		$I_{B1} = -I_{B2} = -10mA$
Output Capacitance	C _{obo}		55	100	pF	V _{CB} = -10V, f = 1MHz

Note: 11. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

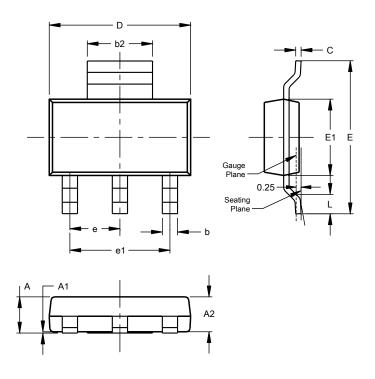




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223 (Type DN)

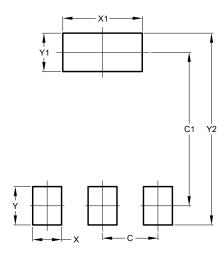


SOT223 (Type DN)					
Dim	Min	Max	Тур		
Α		1.70			
A1	0.01	0.15			
A2	1.50	1.68	1.60		
b	0.60	0.80	0.70		
b2	2.90	3.10			
С	0.20	0.32			
D	6.30	6.70			
Е	6.70	7.30			
E1	3.30	3.70			
е			2.30		
e1			4.60		
L	0.85				
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223 (Type DN)



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
V2	8.00



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